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(54) **SEMICONDUCTOR DEVICE**

(71) Applicant: SAMSUNG ELECTRONICS CO., LTD., Suwon-si (KR)

(72) Inventors: Kiseok Lee, Suwon-si (KR); Keunnam Kim, Suwon-si (KR); Hui-Jung Kim,

Suwon-si (KR)

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(57)ABSTRACT

A semiconductor device including: a device isolation part on a substrate to define first to fourth active regions, the device isolation part interposed between the first and second active regions and the third and fourth active regions; first and second word lines crossing the first and second active regions and adjacent to each other; a first impurity region in the first active region between the first and second word lines; a second impurity region in the first active region at one side of the first word line and spaced apart from the first impurity region; a first conductive pad contacting the first impurity region; a second conductive pad contacting the second impurity region; a bit line on the first conductive pad; a storage node contact on the second conductive pad; and a landing pad on the storage node contact.

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